

BRCS90P03DP

Rev.A .May.-2019

TO-252 P

P-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Electrical Characteristics(Ta=25)

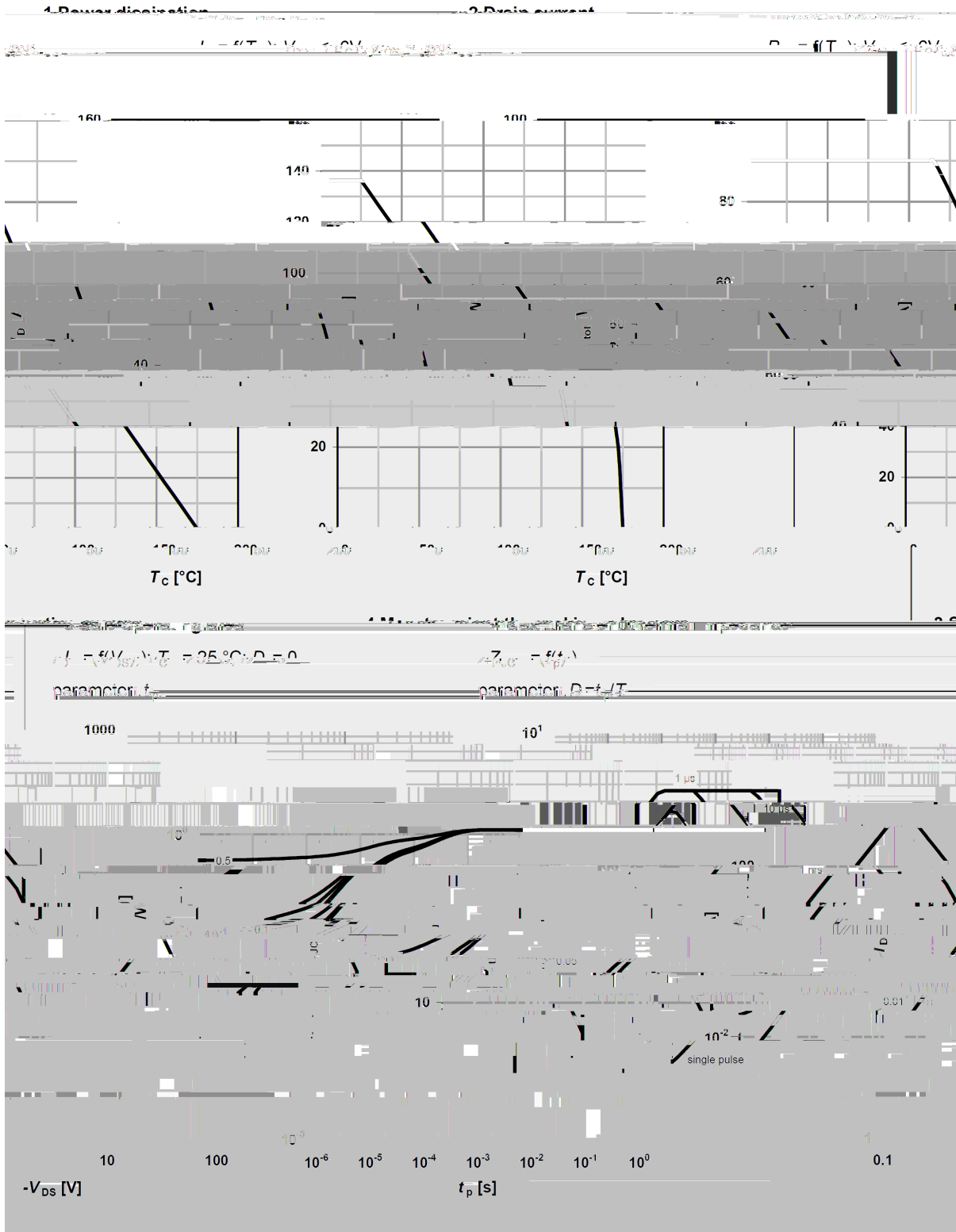
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate to source charge	Q_{gs}	$V_{DD}=-24V, I_D=-90A,$ $V_{GS}=0$ to $-10V$		42	55	nC
Gate to drain charge	Q_{gd}			10	20	nC
Gate charge total	Q_g			100	130	nC
Gate plateau voltage	$V_{plateau}$			-5.3		V
Diode continuous forward current ²⁾	I_S	$T_C=25^{\circ}C$			-90	A
Diode pulse current ²⁾	$I_{S,pulse}$				-360	A
Reverse recovery time ²⁾	t_{rr}	$V_R=-15V, I_F=-50A,$ $di_F/dt =-100A/ s$		50		nS
Reverse recovery charge ²⁾	Q_{rr}			70		nC

1) Current is limited by bondwire; with an $R_{JC} = 1.1K/W$ the chip is able to carry -143A at 25°C.

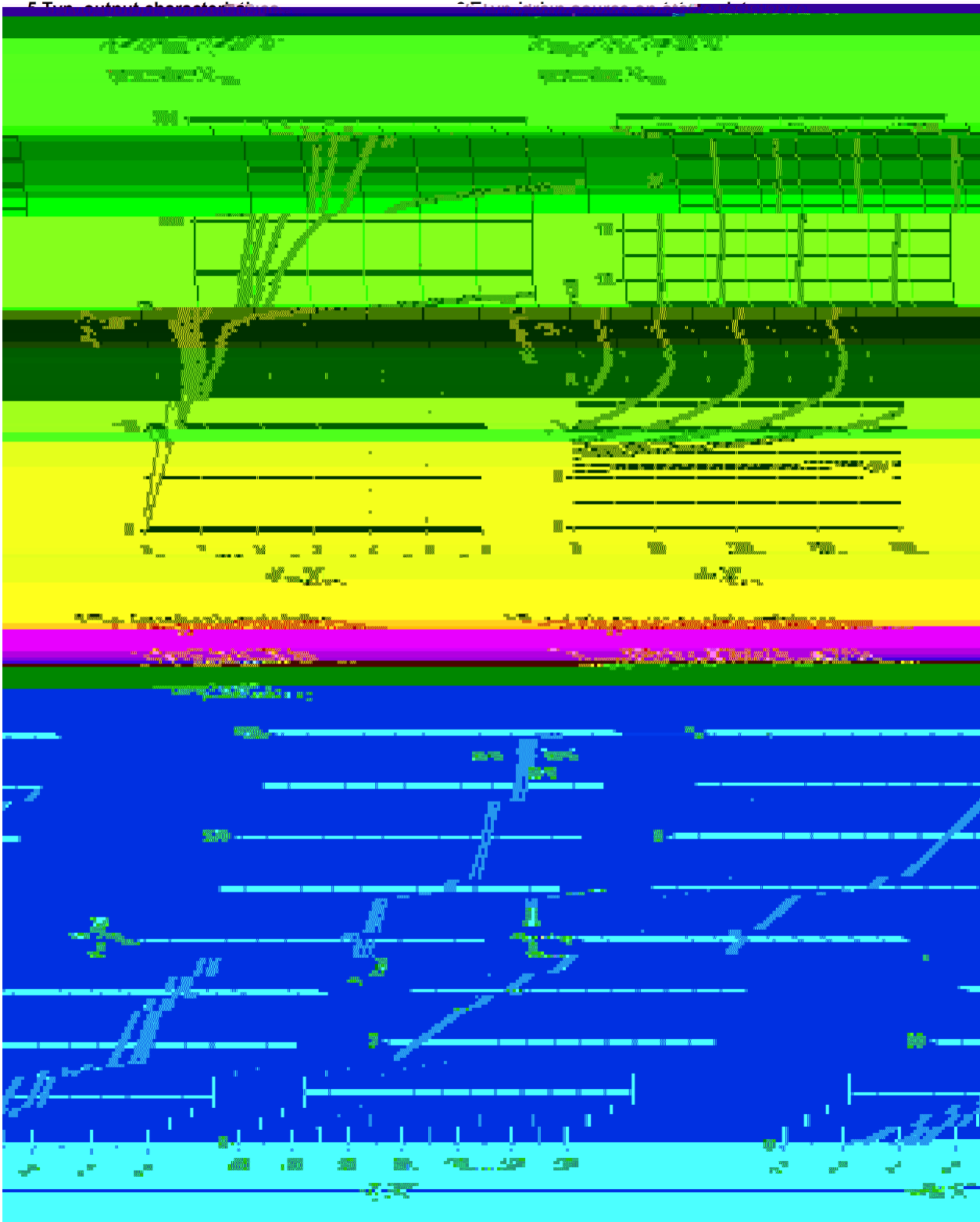
2) Defined by design. Not subject to production test.

3) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

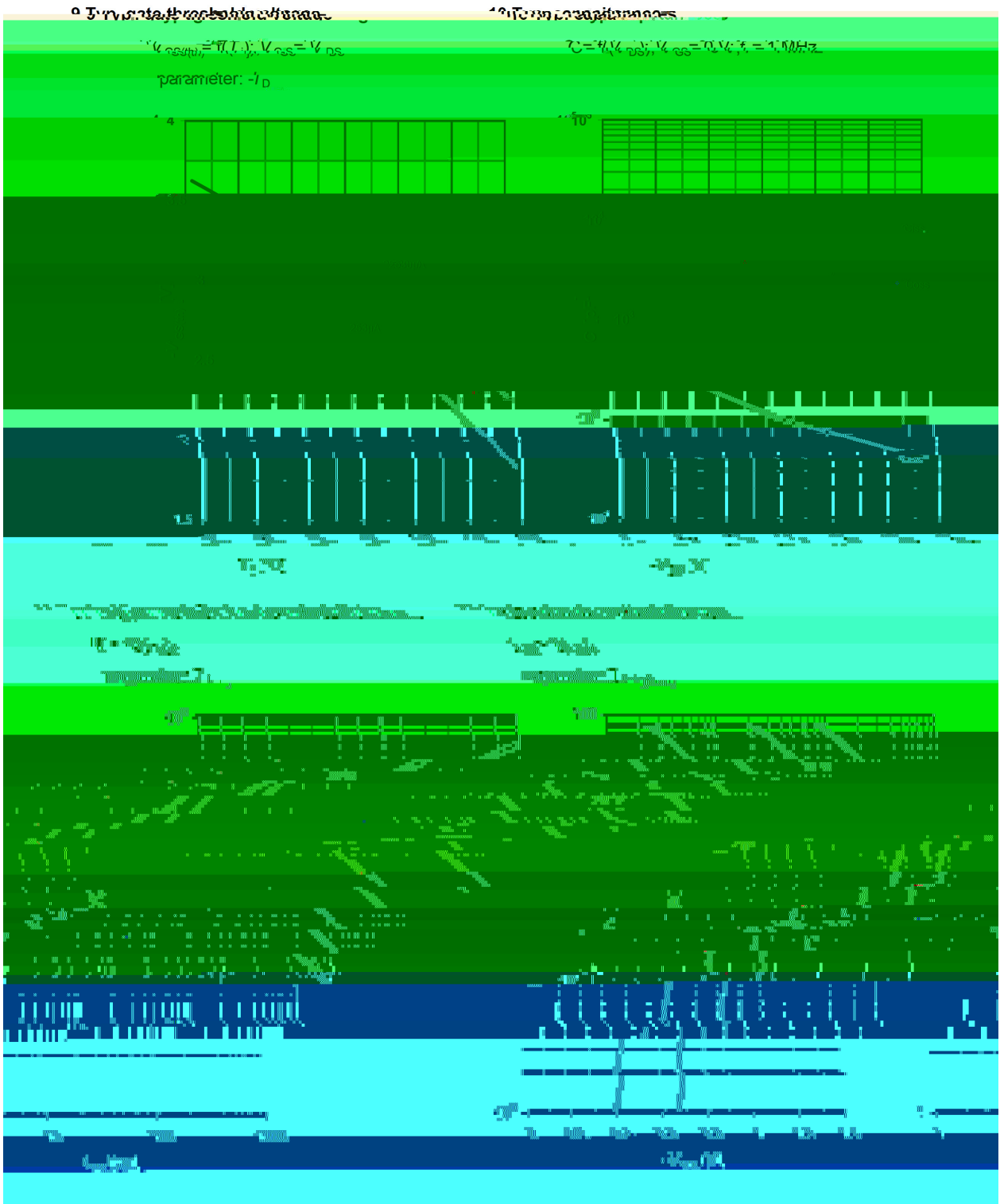
/ Electrical Characteristic Curve



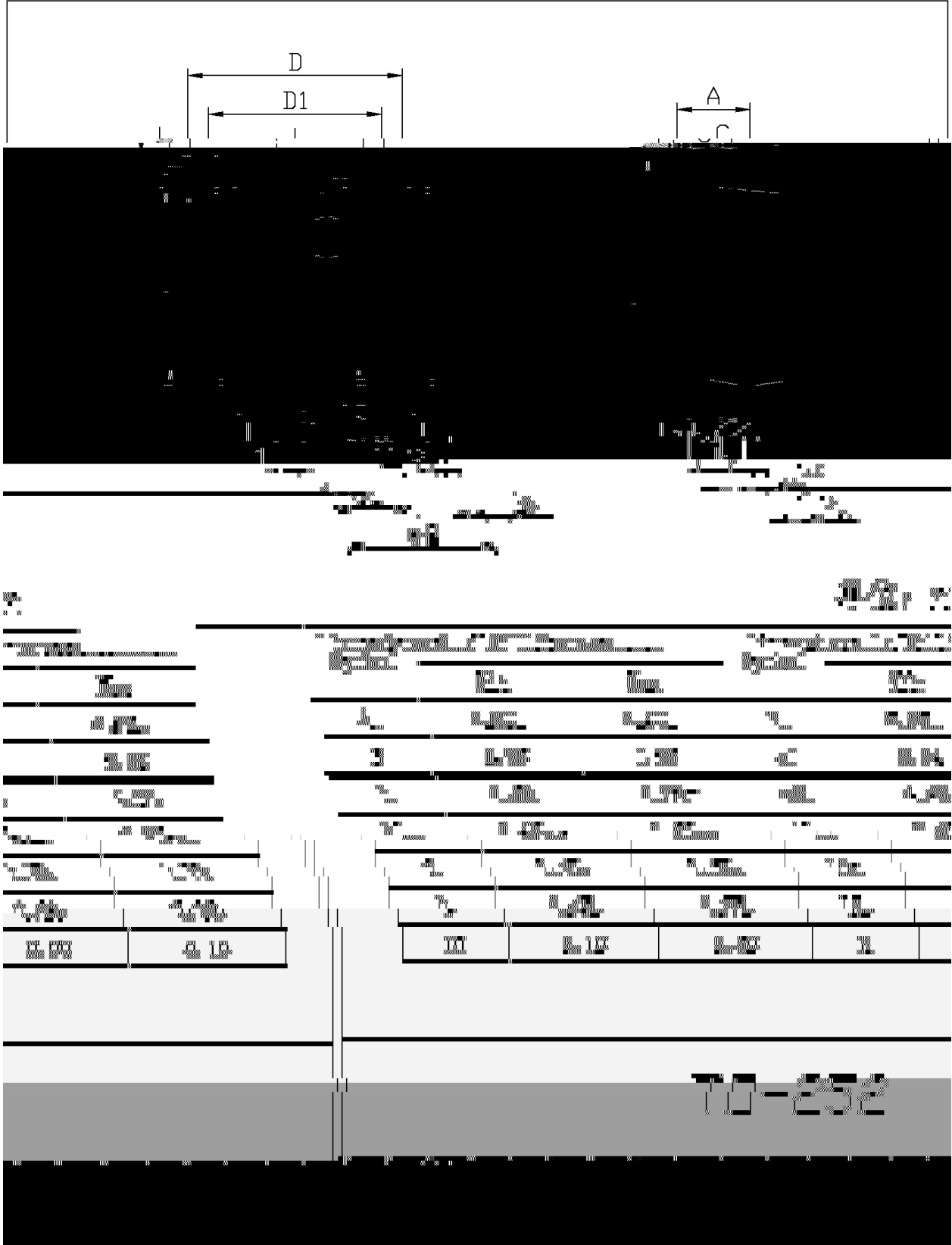
/ Electrical Characteristic Curve



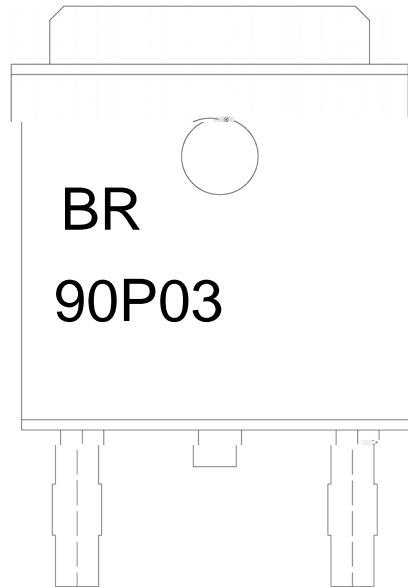
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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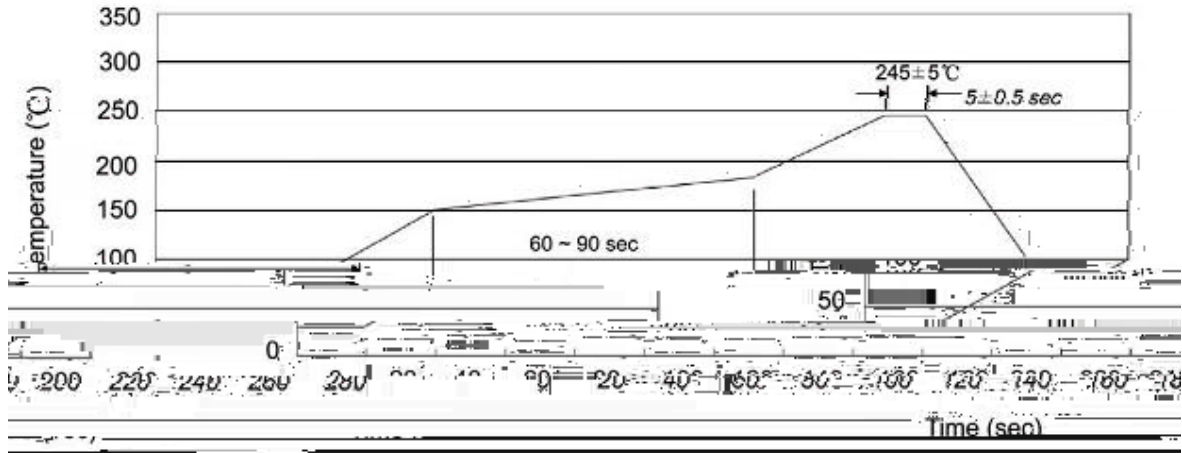
Note:

BR: Company Code

90P03: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ Notices